

Jingsheng Chen

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

79
papers

2,632
citations

30
h-index

49
g-index

86
ext. papers

3,588
ext. citations

10.5
avg, IF

5.47
L-index

#	Paper	IF	Citations
79	Alloy electrode engineering in memristors for emulating the biological synapse.. <i>Nanoscale</i> , 2022 ,	7.7	4
78	Topological Hall transport: materials, mechanisms and potential applications. <i>Progress in Materials Science</i> , 2022 , 100971	42.2	2
77	Enhanced Tunneling Magnetoresistance Effect via Ferroelectric Control of Interface Electronic/Magnetic Reconstructions. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 56638-56644	9.5	
76	An Overview of Ferroelectric Hafnia and Epitaxial Growth. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021 , 15, 2100025	2.5	11
75	Field-free magnetization switching induced by the unconventional spin-orbit torque from WTe ₂ . <i>APL Materials</i> , 2021 , 9, 051114	5.7	8
74	Oxygen vacancy-induced topological nanodomains in ultrathin ferroelectric films. <i>Npj Quantum Materials</i> , 2021 , 6,	5	8
73	Thermal Effect in Current-Induced Magnetization Switching and Out-of-Plane Effective Field Measurements. <i>ACS Applied Electronic Materials</i> , 2021 , 3, 2483-2489	4	3
72	Ferroelectric Self-Polarization Controlled Magnetic Stratification and Magnetic Coupling in Ultrathin LaSrMnO Films. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 30137-30145	9.5	4
71	Prospect of Spintronics in Neuromorphic Computing. <i>Advanced Electronic Materials</i> , 2021 , 7, 2100465	6.4	10
70	Modulation of Spin-Orbit Torque from SrRuO by Epitaxial-Strain-Induced Octahedral Rotation. <i>Advanced Materials</i> , 2021 , 33, e2007114	24	7
69	Spin-Orbit Torque-Induced Domain Nucleation for Neuromorphic Computing. <i>Advanced Materials</i> , 2021 , 33, e2103672	24	10
68	MXene Ti ₃ C ₂ memristor for neuromorphic behavior and decimal arithmetic operation applications. <i>Nano Energy</i> , 2021 , 79, 105453	17.1	22
67	Hf _{0.5} Zr _{0.5} O ₂ -based ferroelectric memristor with multilevel storage potential and artificial synaptic plasticity. <i>Science China Materials</i> , 2021 , 64, 727-738	7.1	11
66	The Future of Memristors: Materials Engineering and Neural Networks. <i>Advanced Functional Materials</i> , 2021 , 31, 2006773	15.6	62
65	Giant spin torque efficiency in single-crystalline antiferromagnet Mn ₂ Au films. <i>Science China Materials</i> , 2021 , 64, 2029-2036	7.1	2
64	Electric Field Control of the Magnetic Weyl Fermion in an Epitaxial SrRuO (111) Thin Film. <i>Advanced Materials</i> , 2021 , 33, e2101316	24	4
63	Symmetry-dependent field-free switching of perpendicular magnetization. <i>Nature Nanotechnology</i> , 2021 , 16, 277-282	28.7	32

62	An Electronic Synapse Based on 2D Ferroelectric CuInP2S6. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000760	7.6	19
61	Magnetic asymmetry induced anomalous spin-orbit torque in IrMn. <i>Physical Review B</i> , 2020 , 101,	3.3	11
60	A van der Waals Synaptic Transistor Based on Ferroelectric Hf0.5Zr0.5O2 and 2D Tungsten Disulfide. <i>Advanced Electronic Materials</i> , 2020 , 6, 2000057	6.4	41
59	Electrical switching of perpendicular magnetization in a single ferromagnetic layer. <i>Physical Review B</i> , 2020 , 101,	3.3	36
58	Perpendicular Magnetic Anisotropy and Dzyaloshinskii-Moriya Interaction at an Oxide/Ferromagnetic Metal Interface. <i>Physical Review Letters</i> , 2020 , 124, 217202	7.4	11
57	A carbon-based memristor design for associative learning activities and neuromorphic computing. <i>Nanoscale</i> , 2020 , 12, 13531-13539	7.7	21
56	Memristors mimicking the regulation of synaptic plasticity and the refractory period in the phenomenological model. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 5183-5190	7.1	2
55	Memristors based on multilayer graphene electrodes for implementing a low-power neuromorphic electronic synapse. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 4926-4933	7.1	12
54	Unusual Hole and Electron Midgap States and Orbital Reconstructions Induced Huge Ferroelectric Tunneling Electroresistance in BaTiO/SrTiO. <i>Nano Letters</i> , 2020 , 20, 1101-1109	11.5	5
53	A Pure 2H-MoS2 Nanosheet-Based Memristor with Low Power Consumption and Linear Multilevel Storage for Artificial Synapse Emulator. <i>Advanced Electronic Materials</i> , 2020 , 6, 1901342	6.4	31
52	Current status and prospects of memristors based on novel 2D materials. <i>Materials Horizons</i> , 2020 , 7, 1495-1518	14.4	59
51	Memristors Based on the Hybrid Structure of Oxide and Boron Nitride Nanosheets Combining Memristive and Neuromorphic Functionalities. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 1900539	2.5	5
50	Designing carbon conductive filament memristor devices for memory and electronic synapse applications. <i>Materials Horizons</i> , 2020 , 7, 1106-1114	14.4	30
49	Ferroic tunnel junctions and their application in neuromorphic networks. <i>Applied Physics Reviews</i> , 2020 , 7, 011304	17.3	54
48	Investigation of Spin Transport Properties in Perpendicularly Magnetized MoS2/Pt/[Co/Ni]n Multilayers with Effective Spin Injection into Two-Dimensional MoS2. <i>Physical Review Applied</i> , 2020 , 14,	4.3	2
47	A Flexible Transient Biomemristor Based on Hybrid Structure HfO2/BSA: Au Double Layers. <i>Advanced Materials Technologies</i> , 2020 , 5, 2000191	6.8	9
46	Thickness and Ferroelectric Polarization Influence on Film Magnetic Anisotropy across a Multiferroic Material Interface. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 44317-44324	9.5	0
45	Role of Interfacial Orbital Hybridization in Spin-Orbit-Torque Generation in Pt-Based Heterostructures. <i>Physical Review Applied</i> , 2020 , 14,	4.3	4

44	Current-induced magnetization switching in all-oxide heterostructures. <i>Nature Nanotechnology</i> , 2019 , 14, 939-944	28.7	64
43	Large spin-orbit torque efficiency enhanced by magnetic structure of collinear antiferromagnet IrMn. <i>Science Advances</i> , 2019 , 5, eaau6696	14.3	37
42	Artificial Synapses Based on Multiterminal Memtransistors for Neuromorphic Application. <i>Advanced Functional Materials</i> , 2019 , 29, 1901106	15.6	121
41	Vacancy-Induced Synaptic Behavior in 2D WS Nanosheet-Based Memristor for Low-Power Neuromorphic Computing. <i>Small</i> , 2019 , 15, e1901423	11	142
40	Flexible Transparent Organic Artificial Synapse Based on the Tungsten/Egg Albumen/Indium Tin Oxide/Polyethylene Terephthalate Memristor. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 18654-18661	9.5	48
39	Strain Effect on Oxygen Evolution Reaction Activity of Epitaxial NdNiO Thin Films. <i>ACS Applied Materials & Interfaces</i> , 2019 , 11, 12941-12947	9.5	36
38	Atomic-Scale Control of Magnetism at the Titanite-Manganite Interfaces. <i>Nano Letters</i> , 2019 , 19, 3057-3065	10.5	10
37	Electronic-reconstruction-enhanced hydrogen evolution catalysis in oxide polymorphs. <i>Nature Communications</i> , 2019 , 10, 3149	17.4	20
36	A Boolean OR gate implemented with an optoelectronic switching memristor. <i>Applied Physics Letters</i> , 2019 , 115, 153504	3.4	10
35	Thickness-dependent polarization-induced intrinsic magnetoelectric effects in La _{0.67} Sr _{0.33} MnO ₃ /PbZr _{0.52} Ti _{0.48} O ₃ heterostructures. <i>Physical Review B</i> , 2019 , 100,	3.3	16
34	Spin-orbit torque in chemically disordered and L11-ordered Cu _{100-x} Ptx. <i>Physical Review Materials</i> , 2019 , 3,	3.2	11
33	Self-Assembled Networked PbS Distribution Quantum Dots for Resistive Switching and Artificial Synapse Performance Boost of Memristors. <i>Advanced Materials</i> , 2019 , 31, e1805284	24	142
32	Control of Synaptic Plasticity Learning of Ferroelectric Tunnel Memristor by Nanoscale Interface Engineering. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 12862-12869	9.5	69
31	Flexible memristors as electronic synapses for neuro-inspired computation based on scotch tape-exfoliated mica substrates. <i>Nano Research</i> , 2018 , 11, 1183-1192	10	69
30	Tuning Bifunctional Oxygen Electrocatalysts by Changing the A-Site Rare-Earth Element in Perovskite Nickelates. <i>Advanced Functional Materials</i> , 2018 , 28, 1803712	15.6	78
29	Graphene Oxide Quantum Dots Based Memristors with Progressive Conduction Tuning for Artificial Synaptic Learning. <i>Advanced Functional Materials</i> , 2018 , 28, 1803728	15.6	156
28	Interface Engineering and Emergent Phenomena in Oxide Heterostructures. <i>Advanced Materials</i> , 2018 , 30, e1802439	24	72
27	Tuning of current-induced effective magnetic field through Rashba effect engineering in hybrid multiferroic structures. <i>NPG Asia Materials</i> , 2018 , 10, 740-748	10.3	7

26	Observation of superconductivity in structure-selected Ti ₂ O ₃ thin films. <i>NPG Asia Materials</i> , 2018 , 10, 522-532	10.3	20
25	From Titanium Sesquioxide to Titanium Dioxide: Oxidation-Induced Structural, Phase, and Property Evolution. <i>Chemistry of Materials</i> , 2018 , 30, 4383-4392	9.6	20
24	Memristor with Ag-Cluster-Doped TiO ₂ Films as Artificial Synapse for Neuroinspired Computing. <i>Advanced Functional Materials</i> , 2018 , 28, 1705320	15.6	221
23	Orthorhombic Ti ₂ O ₃ : A Polymorph-Dependent Narrow-Bandgap Ferromagnetic Oxide. <i>Advanced Functional Materials</i> , 2018 , 28, 1705657	15.6	21
22	Characteristic investigation of a flexible resistive memory based on a tunneling junction of Pd/BTO/LSMO on mica substrate. <i>Applied Physics Letters</i> , 2018 , 113, 223501	3.4	11
21	Epitaxial Ferroelectric Hf _{0.5} Zr _{0.5} O ₂ Thin Films and Their Implementations in Memristors for Brain-Inspired Computing. <i>Advanced Functional Materials</i> , 2018 , 28, 1806037	15.6	98
20	Effect of Extrinsically Introduced Passive Interface Layer on the Performance of Ferroelectric Tunnel Junctions. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 5050-5055	9.5	12
19	Multi-Nonvolatile State Resistive Switching Arising from Ferroelectricity and Oxygen Vacancy Migration. <i>Advanced Materials</i> , 2017 , 29, 1606165	24	64
18	Ultra-low magnetic damping of perovskite La _{0.7} Sr _{0.3} MnO ₃ thin films. <i>Applied Physics Letters</i> , 2017 , 110, 112401	3.4	27
17	Magnetization reversal and magnetoresistance behavior of exchange coupled SrRuO ₃ bilayer. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 215002	3	11
16	Effects of field annealing on Gilbert damping of polycrystalline CoFe thin films. <i>Journal of Magnetism and Magnetic Materials</i> , 2017 , 441, 264-270	2.8	8
15	Highly improved performance in Zr _{0.5} Hf _{0.5} O ₂ films inserted with graphene oxide quantum dots layer for resistive switching non-volatile memory. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 11046-11052 ^{7.1}	7.1	48
14	Giant tunneling electroresistance induced by ferroelectrically switchable two-dimensional electron gas at nonpolar BaTiO ₃ /SrTiO ₃ interface. <i>Physical Review B</i> , 2016 , 94,	3.3	11
13	Tailoring Self-Polarization of BaTiO ₃ Thin Films by Interface Engineering and Flexoelectric Effect. <i>Advanced Materials Interfaces</i> , 2016 , 3, 1600737	4.6	26
12	Ferroelectric HfO ₂ -based materials for next-generation ferroelectric memories. <i>Journal of Advanced Dielectrics</i> , 2016 , 06, 1630003	1.3	108
11	Ferroelectricity and ferroelectric resistive switching in sputtered Hf _{0.5} Zr _{0.5} O ₂ thin films. <i>Applied Physics Letters</i> , 2016 , 108, 232905	3.4	45
10	Ferroelectricity emerging in strained (111)-textured ZrO ₂ thin films. <i>Applied Physics Letters</i> , 2016 , 108, 012906	3.4	34
9	Tunneling electroresistance effect in ultrathin BiFeO ₃ -based ferroelectric tunneling junctions. <i>Applied Physics Letters</i> , 2016 , 109, 242901	3.4	7

8	Ultrathin BaTiO ₃ -based ferroelectric tunnel junctions through interface engineering. <i>Nano Letters</i> , 2015 , 15, 2568-73	11.5	67
7	Functional ferroelectric tunnel junctions on silicon. <i>Scientific Reports</i> , 2015 , 5, 12576	4.9	47
6	Strain Engineering of Octahedral Rotations and Physical Properties of SrRuO ₃ Films. <i>Scientific Reports</i> , 2015 , 5, 10245	4.9	39
5	Multifunctional MoTe ₂ Fe-FET Enabled by Ferroelectric Polarization-Assisted Charge Trapping. <i>Advanced Functional Materials</i> , 2110415	15.6	5
4	Flexible artificial synapse based on single-crystalline BiFeO ₃ thin film. <i>Nano Research</i> , 1	10	4
3	Memristor based on Hg ₂ Se ₃ for emulating biological synaptic plasticity and learning behavior. <i>Science China Materials</i> , 1	7.1	2
2	Controlling Resistance Switching Performances of Hf _{0.5} Zr _{0.5} O ₂ Films by Substrate Stress and Potential in Neuromorphic Computing. <i>Advanced Intelligent Systems</i> , 2100244	6	1
1	A Multifunctional and Efficient Artificial Visual Perception Nervous System with Sb ₂ Se ₃ /CdS-Core/Shell (SC) Nanorod Arrays Optoelectronic Memristor. <i>Advanced Functional Materials</i> , 2203454 ^{15.6}	15.6	6